**Product data sheet** 

#### **Product profile** 1.

### 1.1 General description

Standard level N-channel MOSFET in a SOT404 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

### 1.2 Features and benefits

- AEC Q101 compliant •
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with VGS(th) rating of greater than 1V at 175 °C •

### **1.3 Applications**

- 12 V Automotive systems •
- Electric and electro-hydraulic power steering •
- Motors, lamps and solenoid control •
- Start-Stop micro-hybrid applications
- Transmission control •
- Ultra high performance power switching

### 1.4 Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	30	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	[1]	-	-	120	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	324	W
Static chara	acteristics						
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 11		-	1.23	1.45	mΩ
Dynamic ch	naracteristics	·					
Q <sub>GD</sub>	gate-drain charge	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 24 V; Fig. 13; Fig. 14		-	37	-	nC

#### Table 1 Quick reference data

[1] Continuous current is limited by package.





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# 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain		
3	S	source		G-UFA
mb	D	mounting base; connected to drain		mbb076 S
			D2PAK (SOT404)	

# 3. Ordering information

Table 3. Ordering inf	formation		
Type number	Package		
	Name	Description	Version
BUK761R4-30E	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

### 4. Marking

Table 4. Marking codes	
Type number	Marking code
BUK761R4-30E	BUK761R4-30E

# 5. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	30	V
V <sub>DGR</sub>	drain-gate voltage	R <sub>GS</sub> = 20 kΩ		-	30	V
V <sub>GS</sub>	gate-source voltage	T <sub>j</sub> ≤ 175 °C; DC		-20	20	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>	[1]	-	120	А
		T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>	[1]	-	120	А
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 4		-	1425	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	324	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
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Product data sheet

5 October 2012

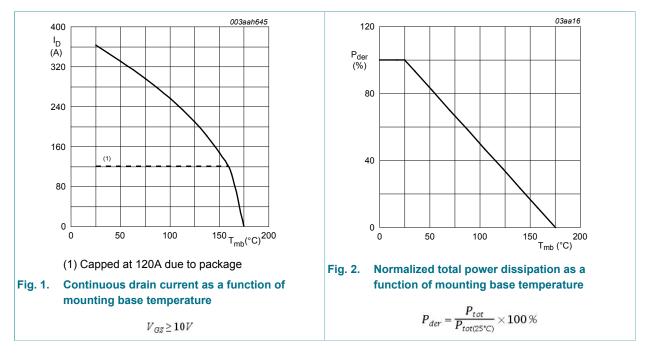
# BUK761R4-30E

#### N-channel TrenchMOS standard level FET

Symbol	Parameter	Conditions		Min	Max	Unit
Source-dra	in diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	120	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$		-	1425	Α
Avalanche	ruggedness					,
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\label{eq:loss} \begin{array}{l} I_{D} = 120 \; A; \; V_{sup} \leq 30 \; V; \; R_{GS} = 50 \; \Omega; \\ V_{GS} = 10 \; V; \; T_{j(\text{init})} = 25 \; ^{\circ}\text{C}; \; \text{unclamped}; \\ \hline \textbf{Fig. 3} \end{array}$	[2][3]	-	1096	mJ

Continuous current is limited by package.
Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[3] Refer to application note AN10273 for further information.



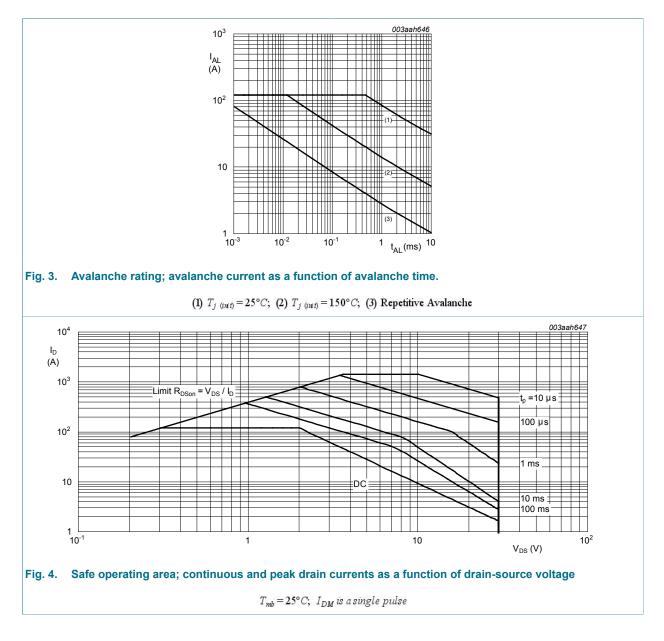
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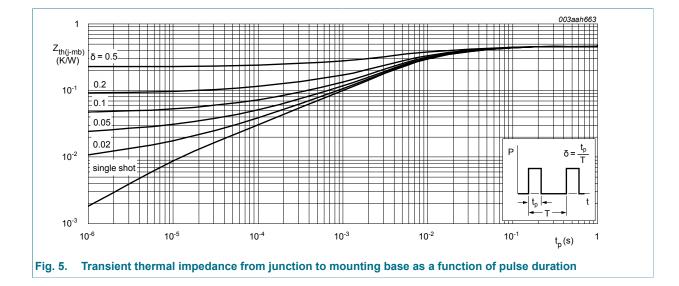
#### **Thermal characteristics** 6.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. <u>5</u>	-	-	0.46	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	minimum footprint ; mounted on a printed-circuit board	-	50	-	K/W

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#### N-channel TrenchMOS standard level FET



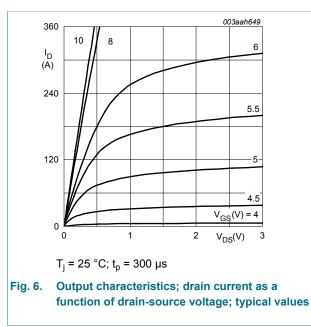
### 7. Characteristics

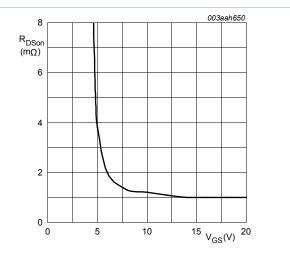
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics	· · · · · ·	I			
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	30	-	-	V
breakdowi	breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	27	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C; Fig. 9; Fig. 10	2.4	3	4	V
	$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = -55 °C; Fig. 10	-	-	4.5	V	
	$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 175 °C; Fig. 10	1	-	-	V	
I <sub>DSS</sub>	G drain leakage current	$V_{DS}$ = 30 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.1	1	μA
	$V_{DS}$ = 30 V; $V_{GS}$ = 0 V; $T_j$ = 175 °C	-	-	500	μA	
I <sub>GSS</sub> gate leakage current	$V_{GS}$ = 20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA	
		$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 11	-	1.23	1.45	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 11; Fig. 12	-	-	2.6	mΩ
Dynamic cl	haracteristics				1	_
Q <sub>G(tot)</sub>	total gate charge	$I_D$ = 25 A; $V_{DS}$ = 24 V; $V_{GS}$ = 10 V;	-	130	-	nC
Q <sub>GS</sub>	gate-source charge	Fig. 13; Fig. 14	-	33	-	nC
Q <sub>GD</sub>	gate-drain charge		-	37	-	nC

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#### N-channel TrenchMOS standard level FET

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz;	-	7184	9580	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u>	-	1710	2052	pF
C <sub>rss</sub>	reverse transfer capacitance		-	956	1282	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 25 \text{ V}; \text{ R}_{L} = 1 \Omega; \text{ V}_{GS} = 10 \text{ V};$ $\text{R}_{G(ext)} = 5 \Omega$	-	31.3	-	ns
t <sub>r</sub>	rise time		-	52.3	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	74.4	-	ns
t <sub>f</sub>	fall time		-	59.7	-	ns
L <sub>D</sub>	internal drain inductance	from upper edge of drain mounting base to center of die	-	2.5	-	nH
L <sub>S</sub>	internal source inductance	from source lead to source bonding pad	-	7.5	-	nH
Source-dra	iin diode		I		1	
V <sub>SD</sub>	source-drain voltage	$I_{S}$ = 25 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; <u>Fig. 16</u>	-	0.78	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S}$ = 20 A; dI <sub>S</sub> /dt = -100 A/µs; V <sub>GS</sub> = 0 V;	-	49	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 25 V	-	66	-	nC







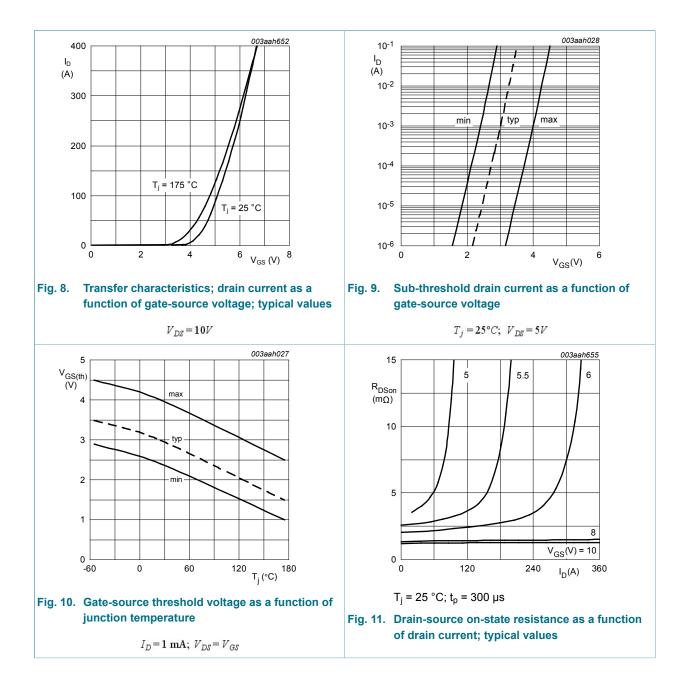
 $T_j = 25^{\circ}C; \ I_D = 25A$ 

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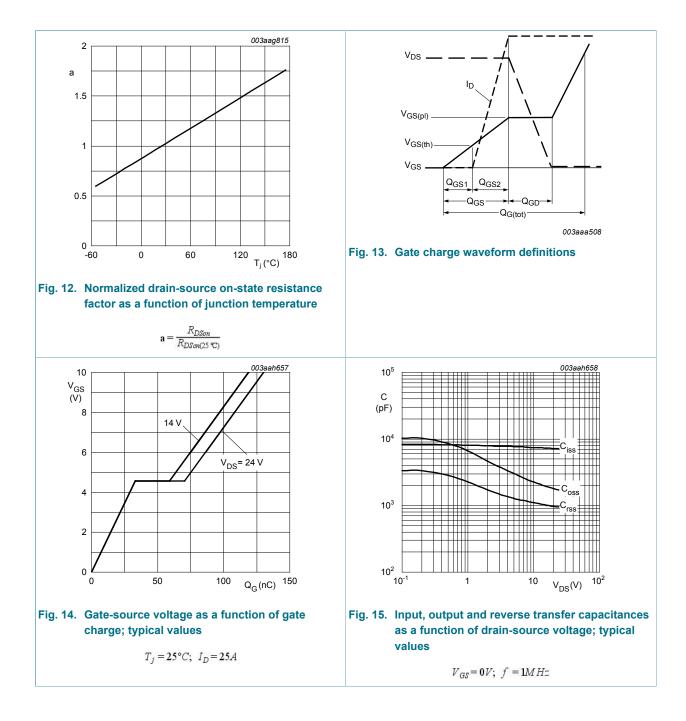
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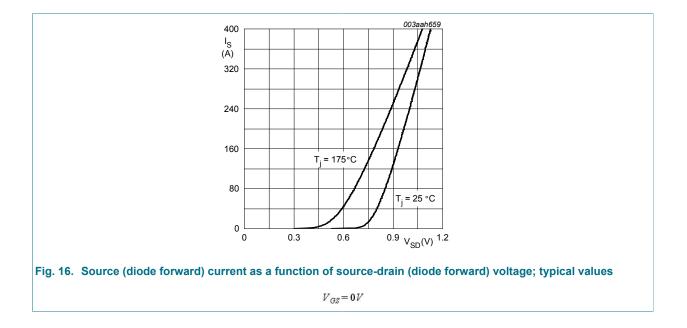
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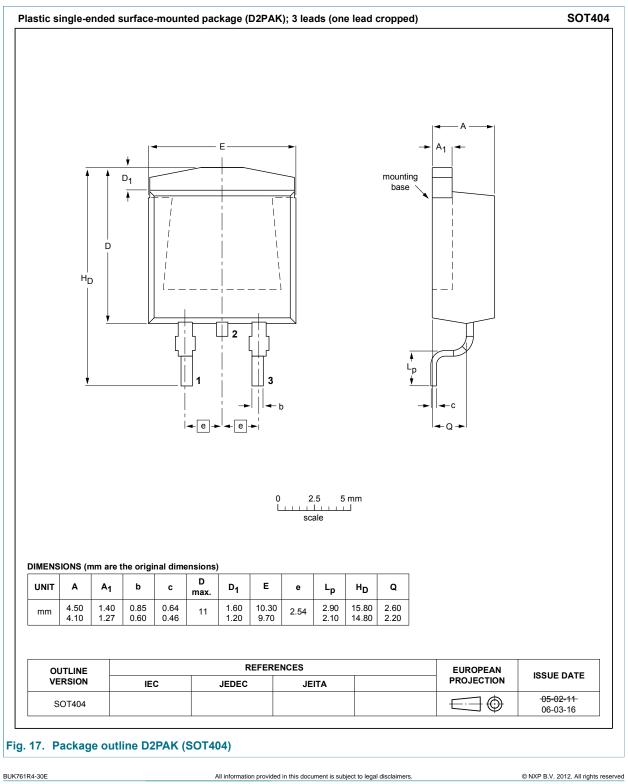
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# 8. Package outline



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### 9. Legal information

#### 9.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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